



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HE13005**HIGH VOLTAGE SWITCH MODE APPLICATION**

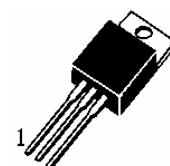
High Speed Switching

Suitable for Switching Regulator and Monitor Control

ABSOLUTE MAXIMUM RATINGS (T_a=25)

T _{stg}	Storage Temperature.....	-65~150
T _j	Junction Temperature.....	150
P _C	Collector Dissipation (T _c =25)	75W
V _{CBO}	Collector-Base Voltage.....	700V
V _{CEO}	Collector-Emitter Voltage.....	400V
V _{EBO}	Emitter-Base Voltage.....	9V
I _C	Collector Current(DC).....	4A
I _C	Collector Current(Pulse)	8A
I _B	Base Current.....	2A

TO-220AB



1 Base , B
2 Collector , C
3 Emitter, E

电参数 (T_a=25)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCEO	Collector-Emitter Breakdown Voltage	400			V	I _C =10mA , I _B =0
I _{EBO}	Emitter Cut-off Current			1	mA	V _{EB} =9V , I _C =0
H _{FE} (1)	DC Current Gain	10		40		V _{CE} =5V , I _C =10A
H _{FE} (2)		8		40		V _{CE} =5V , I _C =2A
V _{CESat1}	Collector- Emitter Saturation Voltage			0.5	V	I _C =1A , I _B =0.2A
V _{CESat2}				0.6	V	I _C =2A , I _B =0.5A
V _{CESat3}				1	V	I _C =4A , I _B =1A
V _{BESat1}	Base-Emitter Saturation Voltage			1.2	V	I _C =1A , I _B =0.2A
V _{BESat2}				1.6	V	I _C =2A , I _B =0.5A
C _{ob}	Output Capacitance		65		pF	V _{CB} =10V , f=0.1MHz
f _r	Current Gain-Bandwidth Product	4			MHz	V _{CE} =10V , I _C =0.5A
t _{ON}	Turn-On Time			0.8	μS	
t _{STG}	Storage Time			4	μS	
t _F	Fall Time			0.9	μS	
						V _{CC} =125V , I _C =2A I _{B1} =- I _{B2} =0.4A

hfe Classification : H1(10--16) H2(14--21) H3(19--26) H4(24--31) H5(29--40)



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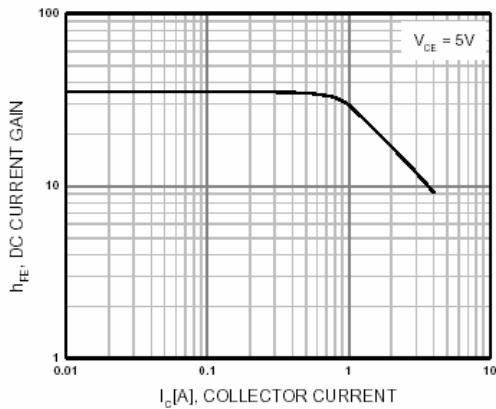


Figure 1. DC current Gain

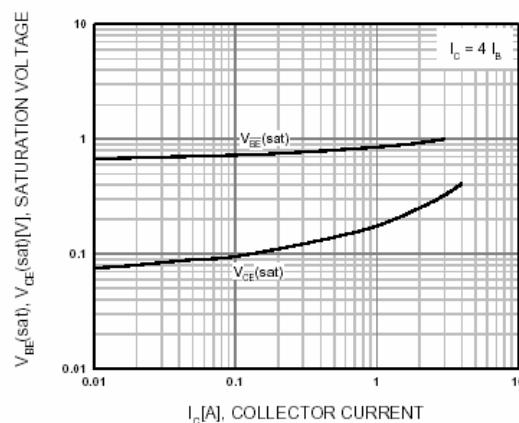


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

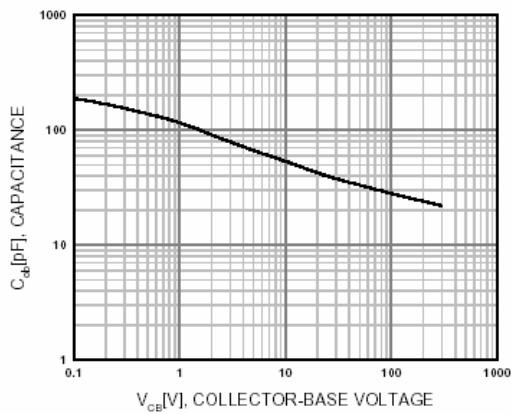


Figure 3. Collector Output Capacitance

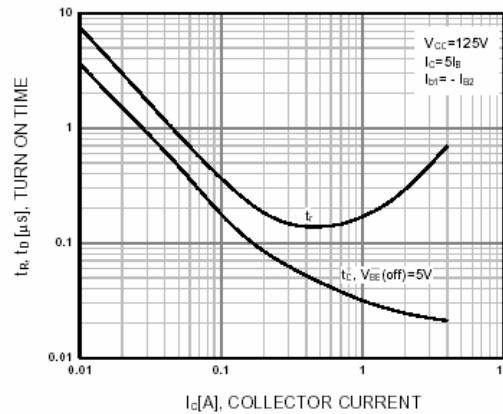


Figure 4. Turn On Time

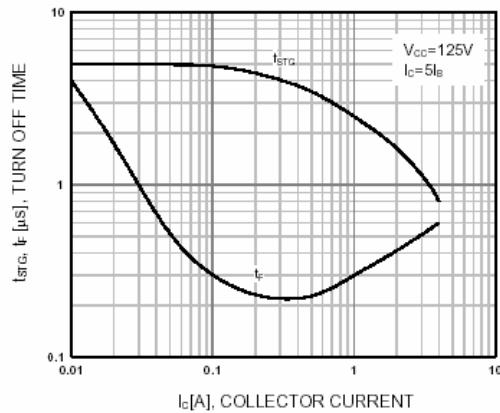


Figure 5. Turn Off Time

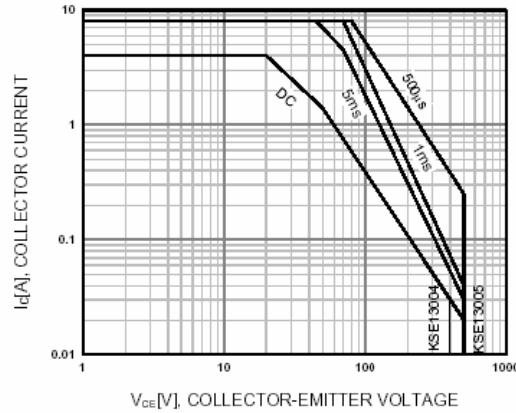


Figure 6. Safe Operating Area



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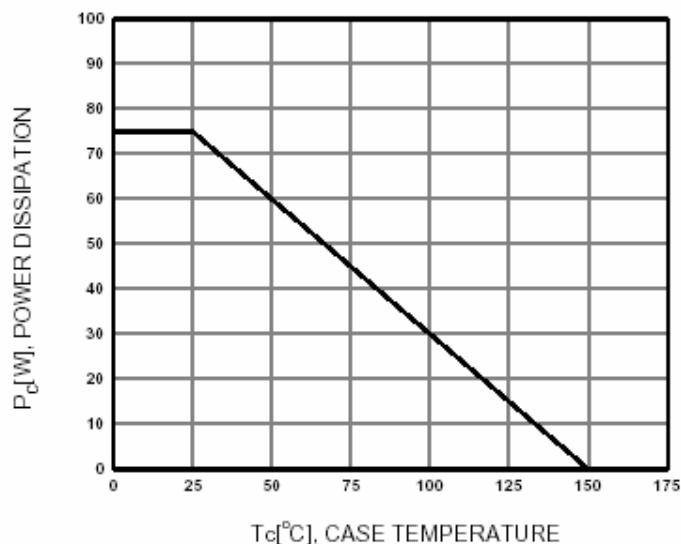


Figure 7. Power Derating